ICMOVPE
XXII July 12-17, 2026
ICC JEJU, Jeju Island, Korea

Session Title:	**[MoB1] Nitrides for Electronics - I**
Session Date:	**July 13 (Mon.), 2026**
Session Time:	**11:15-12:30**
Session Room:	**Room B (Baekrok Hall B-2, 1F)**
Session Chairs	

[MoB1-1] [Invited] **11:15-11:45**

Recent Progress and Device Advantages of N-Polar GaN/AlN HEMTs

N. Okada[1], F. Yamanaka[1], A. H. Zazuli[1], M. Feng[1], T. Kimoto[1], R. Ninoki[1], N. Hirata[1], H. Danbata[1], A. Hayashiuchi[1], K. Sunai[1], H. Tokumoto[1], Y. Kitamura[1], S. Kurai[1], M. Hiroki[2], K. Hirama[2], Y. Taniyasu[2], and Y. Yamada[1], [1] Yamaguchi University, Japan, [2] NTT, Inc., Japan

[MoB1-2] [Invited] **11:45-12:15**

MOCVD Growth of III-Nitride Using New Precursors for HEMT: Challenges and Progress

Byeongchan So, Teresa Duarte, Hanspeter Menner, Jannik Richter, Lutz Kirste, Mario Prescher, Patrik Straňák, Sven Maegdefessel, Felix Hoffmann, Fouad Benkhelifa, Stefano Leone, and Rüdiger Quay, Fraunhofer Institute for Applied Solid State Physics IAF, Germany

[MoB1-3] **12:15-12:30**

Tunable High-Temperature MOCVD Growth for Strain-Controlled AlN-Based RF GaN HEMT Epitaxy

JongJin Jang, SeongCheol Choi, and DongSik Seo, TES. Co. Ltd, Korea